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Expedited Procedure  
Examining Group 1762  
Docket No: 740756-1614

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of )  
Takeshi FUKUNAGA et al. )  
Serial No.: 08/781,920 )  
Filed: December 30, 1998 )  
For: METHOD OF FABRICATING A )  
SEMICONDUCTOR DEVICE UTILIZING )  
A CATALYST MATERIAL SOLUTION )

#330K  
JUN 06 2001  
Group Art Unit: 1762

Examiner: M. PADGETT

CORRECTED AMENDMENT

Commissioner for Patents  
Washington, D. C. 20231

Sir:

Responsive to the Office Action of **December 6, 2000** and Notice of Non-Compliant Amendment of May 14, 2001, the period for response having been extended a further three (3) months until June 6, 2001, the following corrected amendments and remarks are respectfully submitted in connection with the above-identified application.

IN THE SPECIFICATION:

On page 33, replace the second full paragraph with the following:

*KJ*  
Thereafter, the substrate is subjected to annealing by laser light irradiation. Although a KrF excimer laser (wavelength: 248 nm; pulse width: 20 nsec) is used in this embodiment, other lasers may also be used. As for the laser light irradiation conditions, the energy density is 200 to 400 mJ/cm<sup>2</sup>, for instance, 250 mJ/cm<sup>2</sup>, and 2 to 10 shots, for instance, 2 shots, are applied per one location. The annealing effect may be enhanced by heating the substrate to 200 to 450°C during the irradiation (Fig. 5(C)).

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